PBSS5240Z 40 V, 2 A PNP low VCEsat (BISS) transistor 15 October 2014

Product data sheet

General description 1.

PNP low V_{CFsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4240Z

2. **Features and benefits**

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-40	V
I _C	collector current		-	-	-2	Α
I _{CM}	peak collector current	$t_p \le 1$ ms; single pulse	-	-	-3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	320	mΩ



40 V, 2 A PNP low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2, 4
2	С	collector		1—
3	Е	emitter		. M
4	С	collector	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	3 sym028

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5240Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5240Z	S5240Z

40 V, 2 A PNP low VCEsat (BISS) transistor

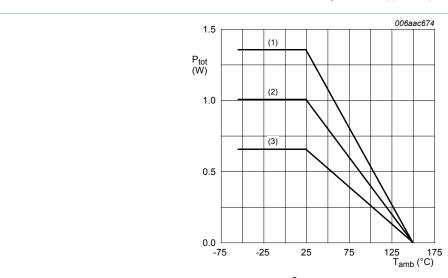
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-40	V
V_{CEO}	collector-emitter voltage	open base		-	-40	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-2	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	-3	Α
I _B	base current			-	-300	mA
I _{BM}	peak base current	t _p ≤ 1 ms; single pulse		-	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1	W
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fro	thermal resistance	in free air	[1]	-	-	192	K/W
	from junction to ambient		<u>[2]</u>	-	-	125	K/W
	umbient		[<u>3</u>]	-	-	93	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

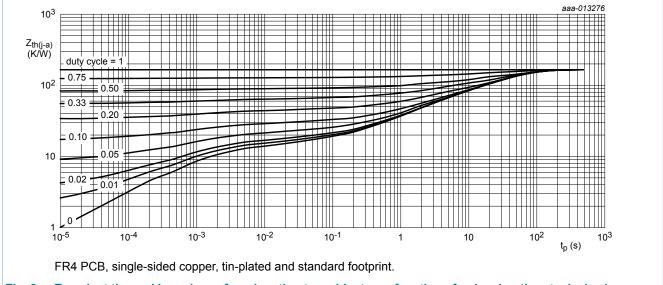
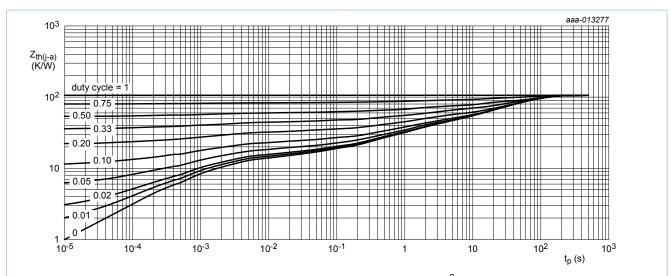


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

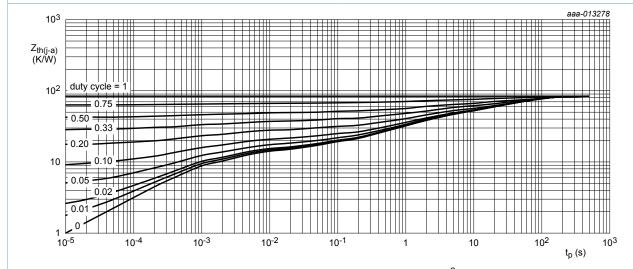
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40 V, 2 A PNP low VCEsat (BISS) transistor



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

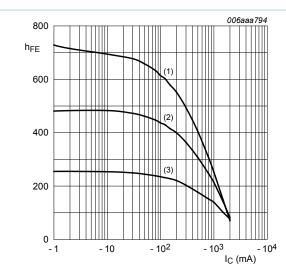
40 V, 2 A PNP low VCEsat (BISS) transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -32 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	$V_{CB} = -32 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -32 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
Гево	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -1 mA; T_{amb} = 25 °C	300	-	-	
		V_{CE} = -5 V; I_{C} = -500 mA; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	215	-	-	
		V_{CE} = -5 V; I_{C} = -1 A; t_{p} ≤ 300 μ s; δ ≤ 0.02; T_{amb} = 25 °C	145	-	-	
		V_{CE} = -5 V; I_{C} = -2 A; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C; pulsed	55	-	-	
V _{CEsat}	collector-emitter	I _C = -100 mA; I _B = -1 mA; T _{amb} = 25 °C	-	-	-140	mV
	saturation voltage	I_C = -500 A; I_B = -50 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_{amb} = 25 °C	-	-	-170	mV
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02; T_{amb} = 25 ^{\circ}C$	-	-	-320	mV
		I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02; T_{amb}$ = 25 °C	-	-	-650	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-	320	mΩ
V_{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \mu\text{s}; \ \delta \le 0.02; \ T_{amb} = 25 ^{\circ}\text{C}$	-	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02; T_{amb} = 25 \text{ °C}$	-	-	-1.1	V
fт	transition frequency	V _{CE} = -10 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	150	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	12	pF

40 V, 2 A PNP low VCEsat (BISS) transistor



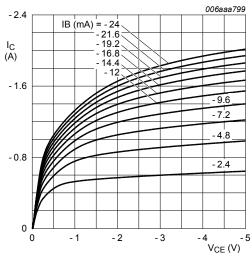
$$V_{CE}$$
 = -5 V

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

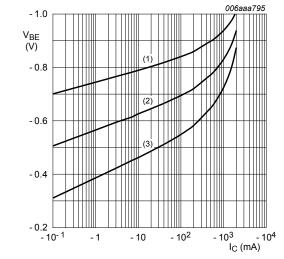
(3)
$$T_{amb} = -55$$
 °C

Fig. 5. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



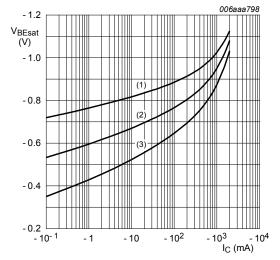
$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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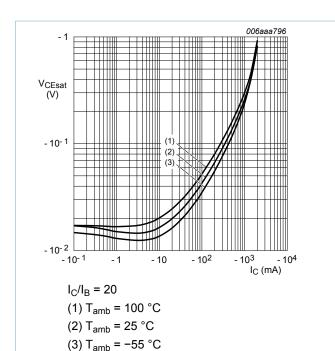


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

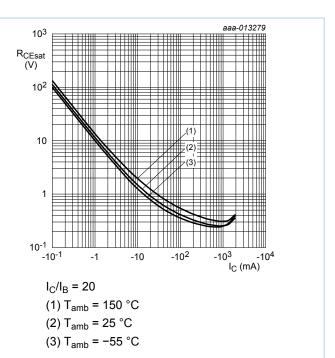


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline

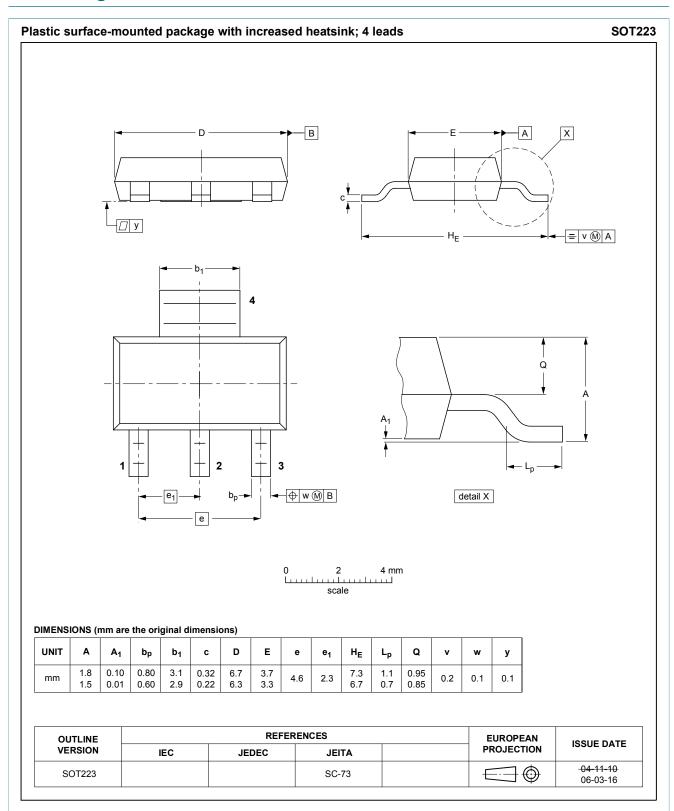


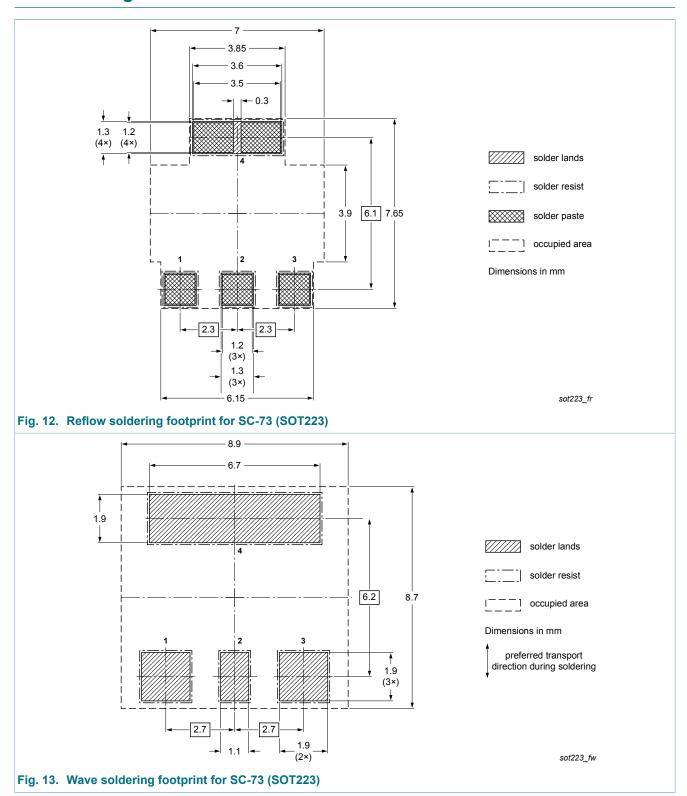
Fig. 11. Package outline SC-73 (SOT223)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5240Z v.1	20141015	Product data sheet	-	-

40 V, 2 A PNP low VCEsat (BISS) transistor

15. Legal information

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40 V, 2 A PNP low VCEsat (BISS) transistor

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40 V, 2 A PNP low VCEsat (BISS) transistor

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	8
11.1	Quality information	8
12	Package outline	9
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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